

<b>Form 1449 (Modified)</b>		Atty Docket No. <b>ALSCP003</b>	Application No.: <b>09/375,702</b>
<b>Information Disclosure Statement By Applicant</b>		Applicant: <b>Perumal Ratnam</b>	O I P E MAR 07 2000 JC46 PATENT & TRADEMARK OFFICE
(Use Several Sheets if Necessary)		Filing Date <b>August 16, 1999</b>	
		Group <b>2812</b>	

### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
<i>MR</i>	A1	5,120,671	6/9/92	Tang, <i>et al.</i>	437	43	11/29/90
<i>MR</i>	A2	5,470,773	11/28/95	Liu, <i>et al.</i>	437	43	4/25/94

### Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation
							Yes No

### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>MR</i>	C1	Chang, <i>et al.</i> , "Corner-Field Induced Drain Leakage In Thin Oxide MOSFETs," <i>IEDM Technical Digest</i> , 31.2, pp. 714-17 (1987).
<i>MR</i>	C2	Kume, <i>et al.</i> , "A Flash-Erase EEPROM Cell With An Asymmetric Source and Drain Structure," <i>IEDM Technical Digest</i> , 25.8, pp. 560-63 (1987).
<i>MR</i>	C3	Yokozawa, <i>et al.</i> , "Low-Field-Stress Erasing Scheme for Highly-Reliable Flash Memories," NEC ULSI Device Development Laboratories, 24 pages, February 12, 1997.
Examiner		Date Considered <i>5m</i>

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.